

**AMENDMENTS TO THE CLAIMS**

Please cancel claims 1-8 without prejudice or disclaimer of their underlying subject matter.

1-8. (Canceled)

Please add the following new claims.

9. (New) A method for manufacturing a bipolar transistor, the method comprising the steps of:

forming a base layer on an insulator, said base layer being in contact with a portion of a semiconductor substrate;

forming an insulating film on said base layer;

forming base and opening electrode lead openings within said insulating film, said base electrode lead opening being formed simultaneous with said emitter electrode lead opening;

depositing a conducting film into said base electrode lead opening and into said emitter electrode lead opening, said conducting film within said base electrode lead opening being a base electrode lead portion and said conducting film within said emitter electrode lead opening being an emitter electrode lead portion; and thereafter,

polishing said conducting film to separate said base electrode lead portion from said emitter electrode lead portion.

10. (New) The method for manufacturing a bipolar transistor as described in claim 9, wherein said insulator is on said semiconductor substrate, an opening within said insulator exposing said portion of the semiconductor substrate.

11. (New) The method for manufacturing a bipolar transistor as described in claim 9, wherein said base layer is a semiconductor material.

12. (New) The method for manufacturing a bipolar transistor as described in claim 9, wherein said conducting film is deposited simultaneously into said base and emitter electrode lead openings.

13. (New) The method for manufacturing a bipolar transistor as described in claim 9, further comprising the step of:

diffusing a dopant from said emitter electrode lead portion into said base layer to form an emitter region with said base layer.

14. (New) The method for manufacturing a bipolar transistor as described in claim 9, further comprising the step of:

depositing a silicide onto a polished surface of said conducting film.

15. (New) The method for manufacturing a bipolar transistor as described in claim 14, further comprising the step of:

depositing an interlayer insulator onto said silicide and said insulating film.